

ABSTRACT OF THE DISCLOSURE

A dry etching apparatus including a plate 15 provided in parallel or nearly parallel with an RF electrode 9 to cover a substrate 1 placed on the RF electrode 9 directly or through a tray 24. The plate 15 is provided with planar or nearly planar obstacles 16 that inhibit a gas and plasma from passing through the plate 15 as well as opening portions 19. This makes it possible to achieve conditions under which etching residues attach to the surface of the substrate faster by trapping the etching residues in a space between the surface of the substrate 1 and the plate 15. Fine textures can be thus formed efficiently on the surface of the substrate (Fig. 4).